

FIG. 1

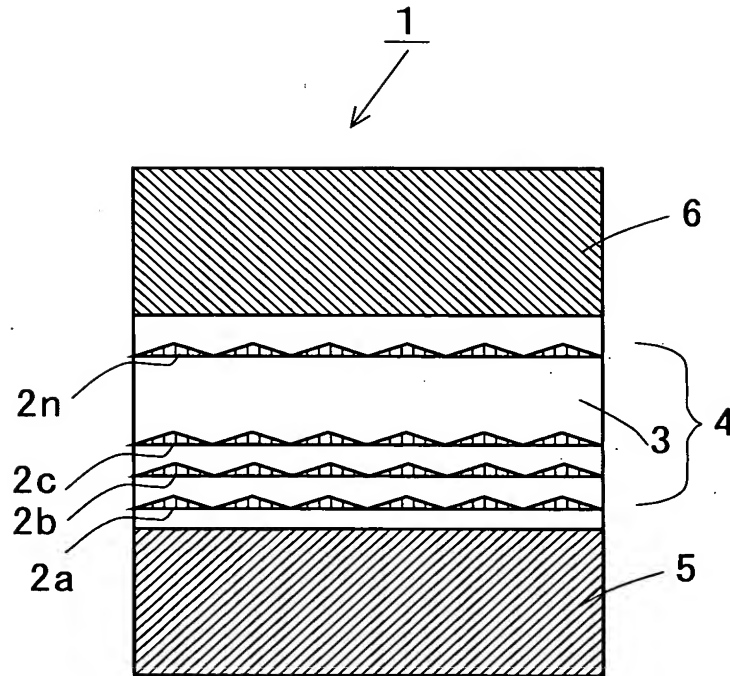


FIG. 2

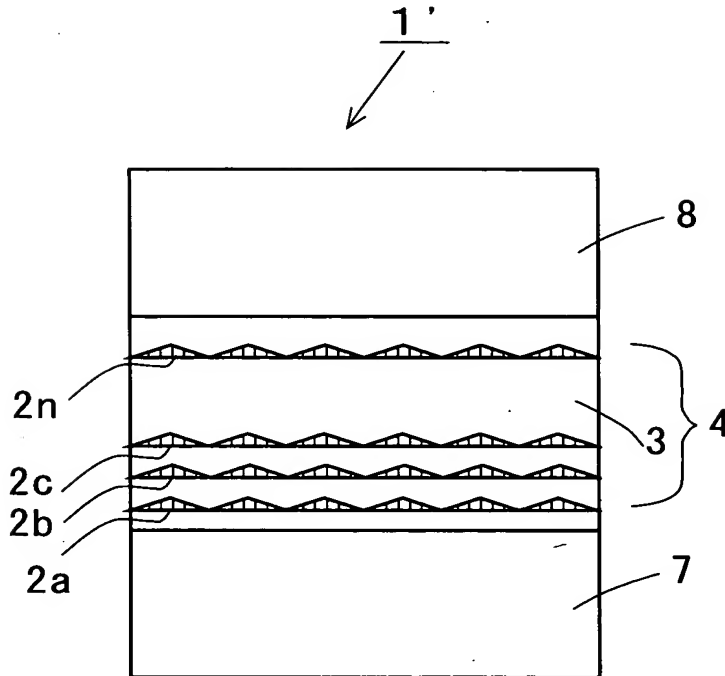


FIG. 3

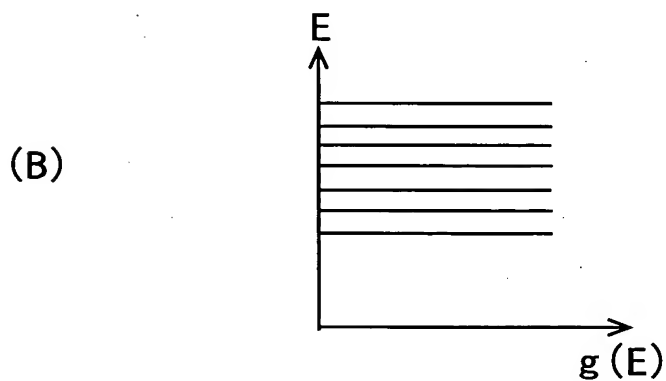
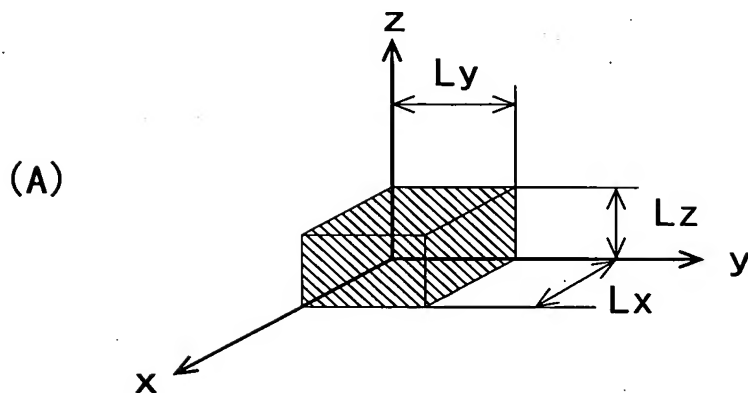


FIG. 4

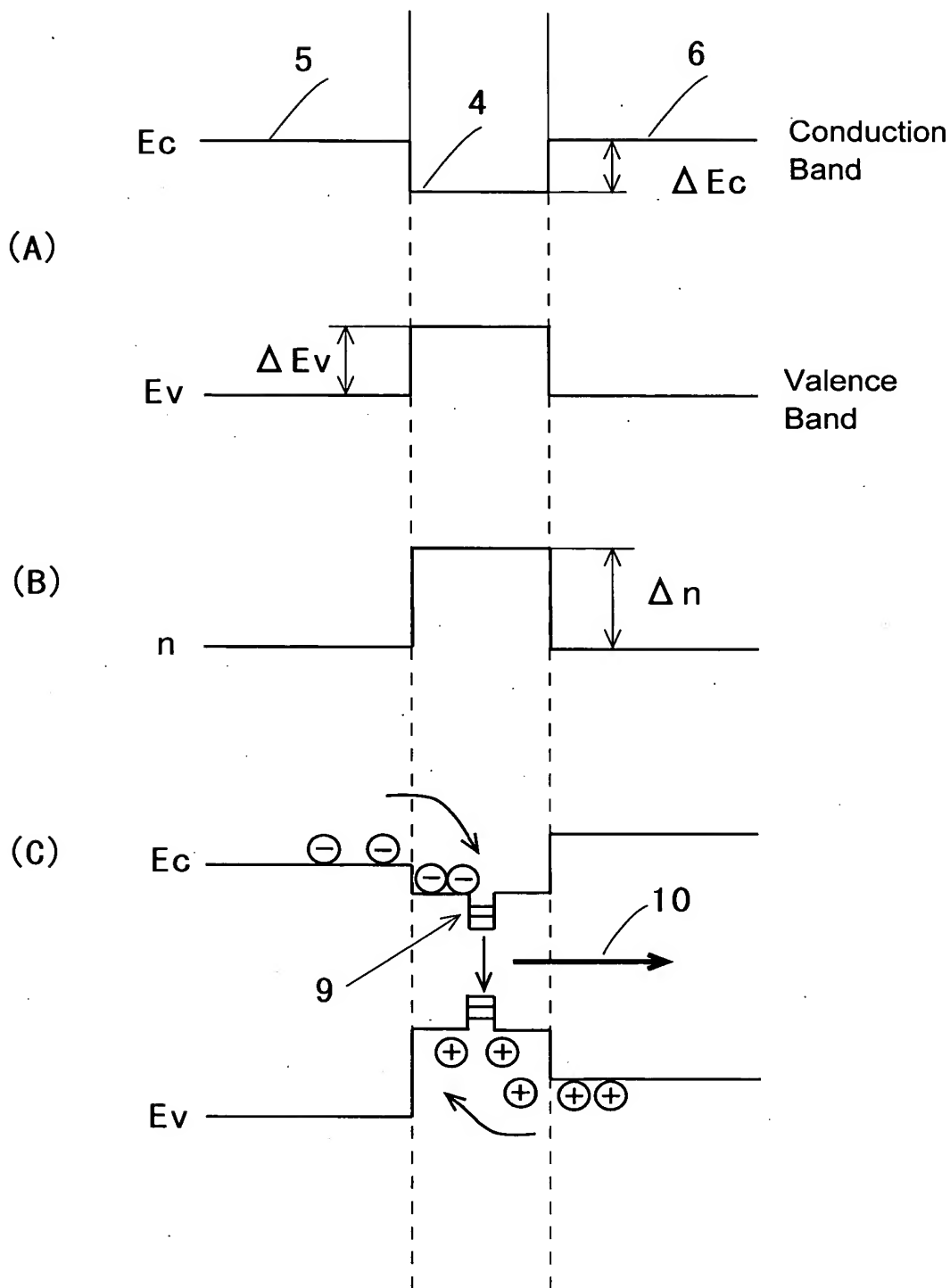


FIG. 5

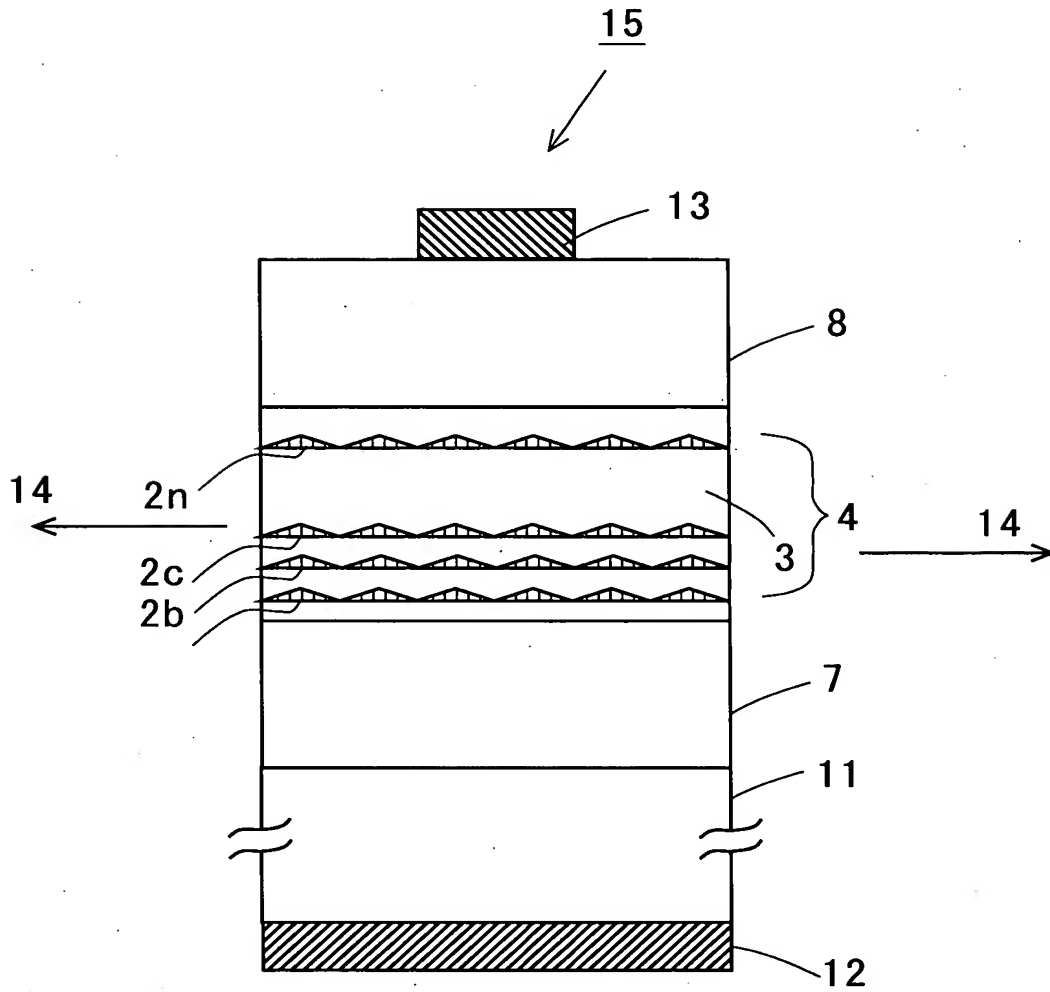


FIG. 6

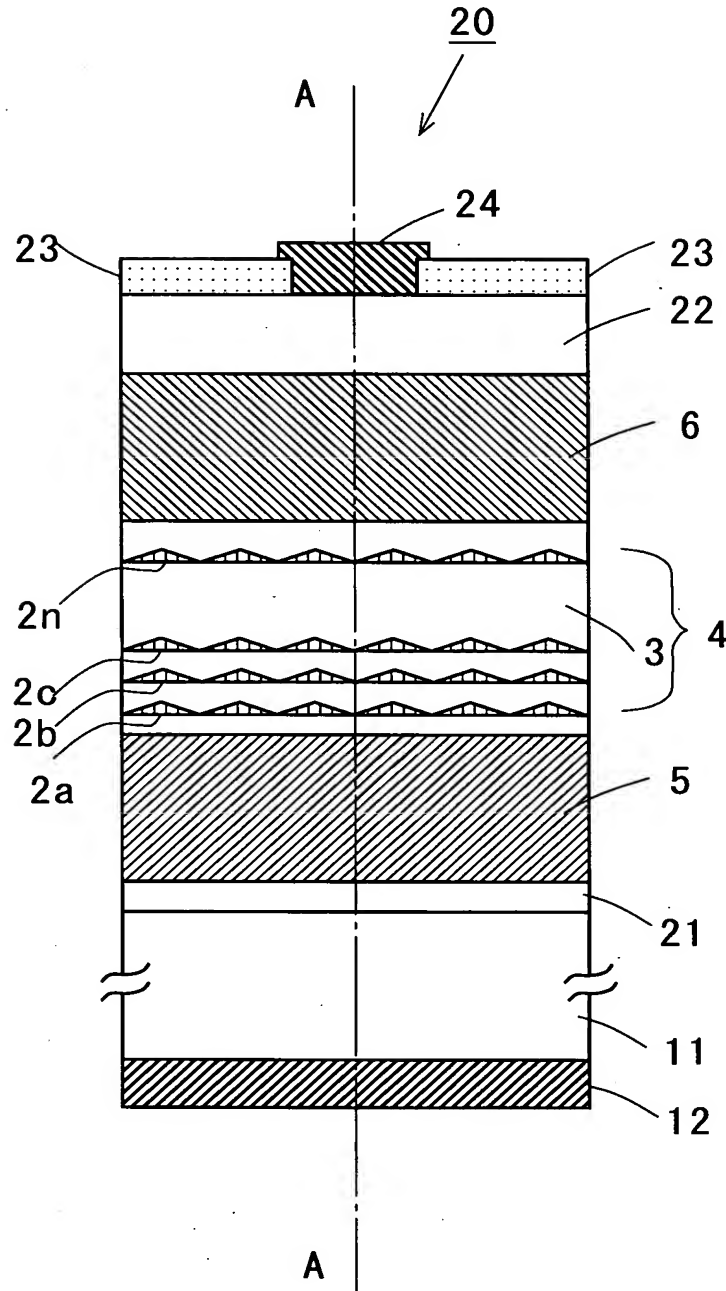


FIG. 7

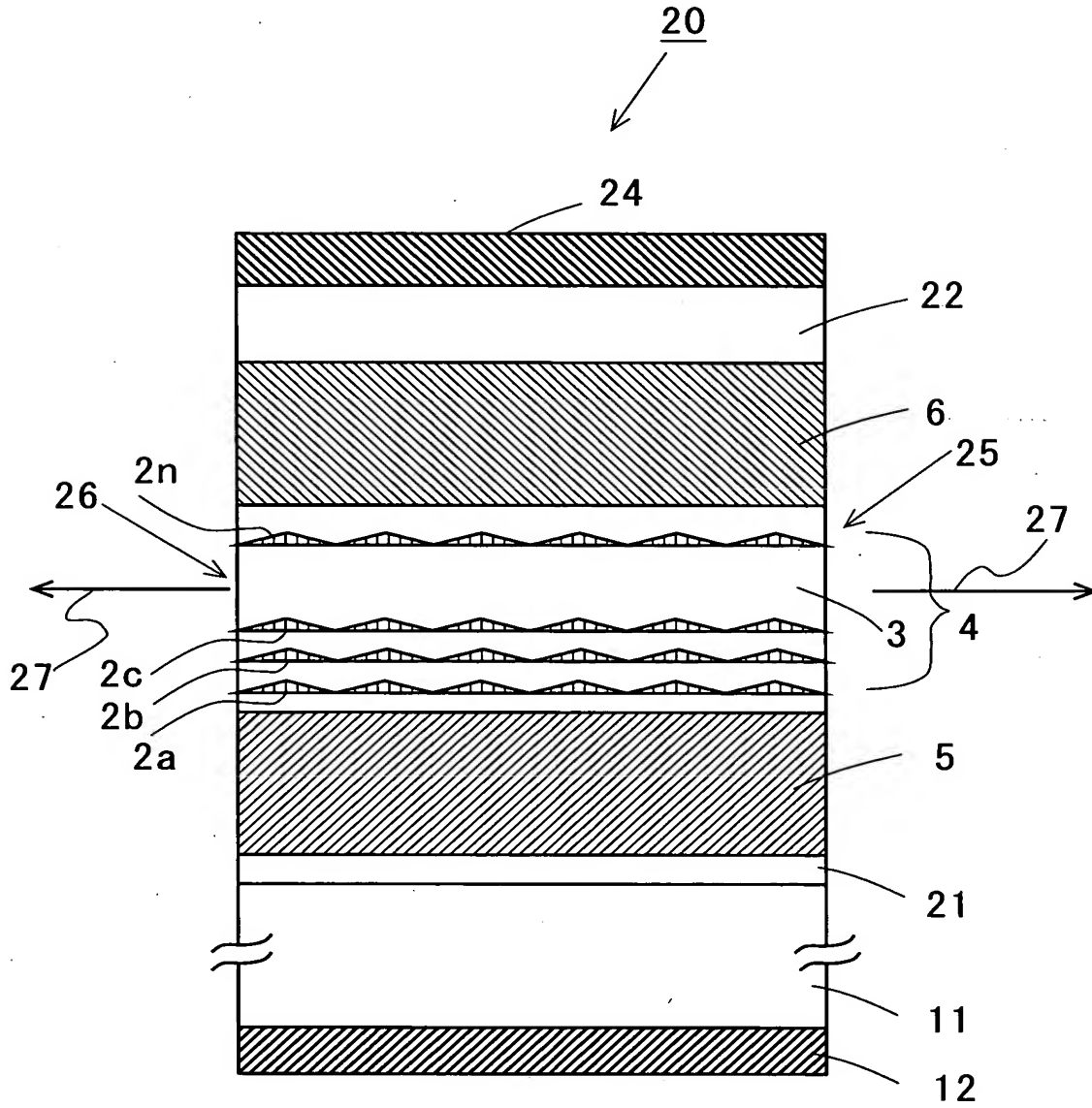


FIG. 8

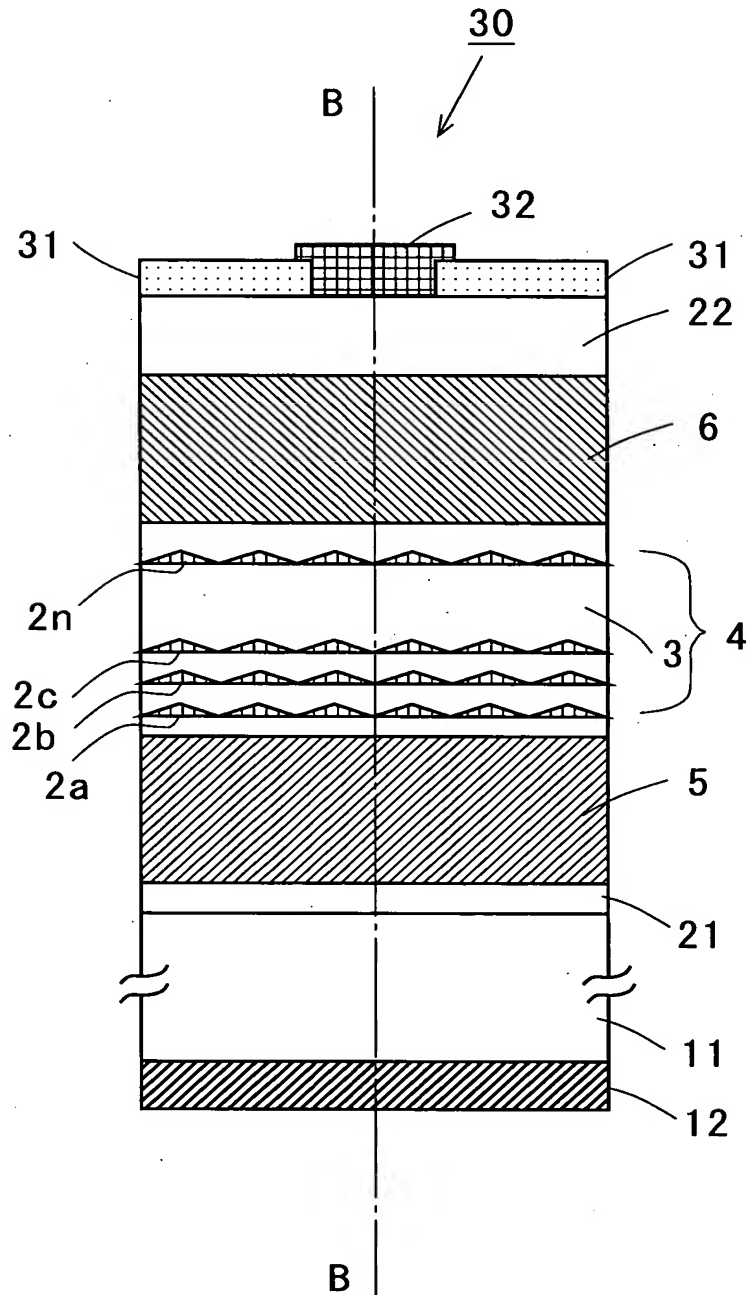




FIG. 9

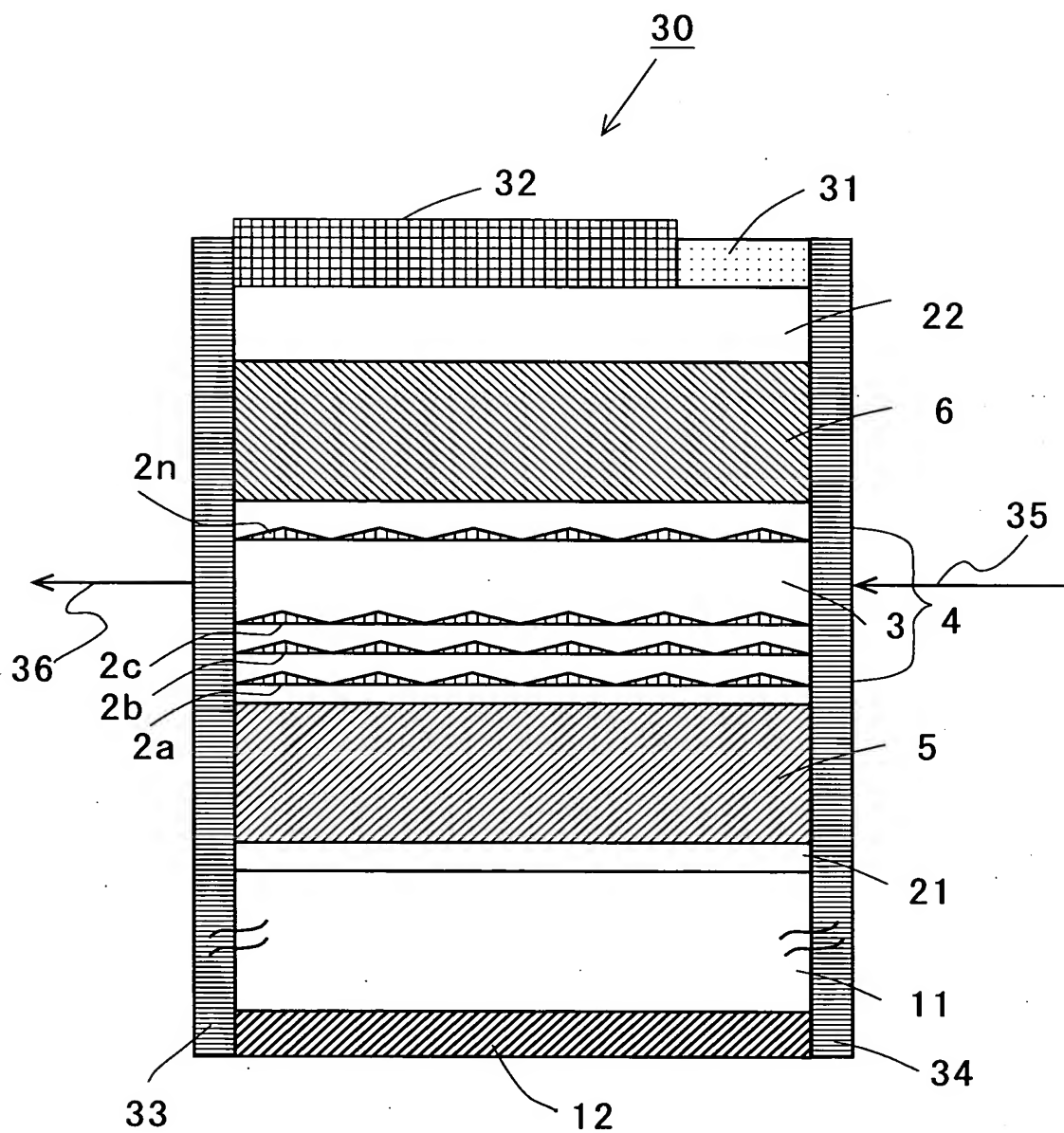


FIG. 10

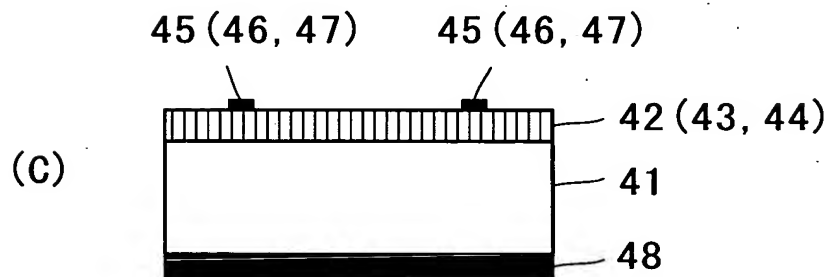
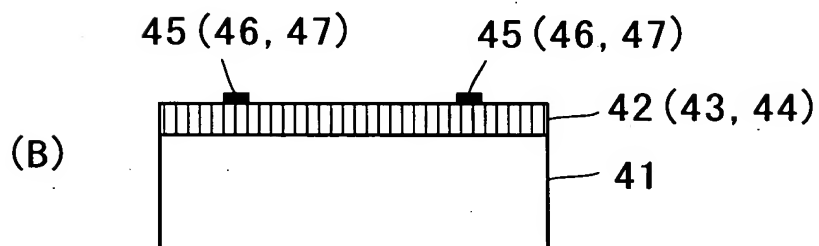
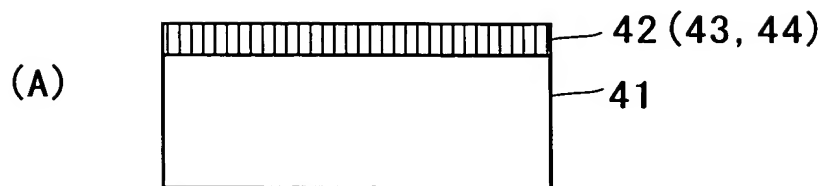


FIG. 11

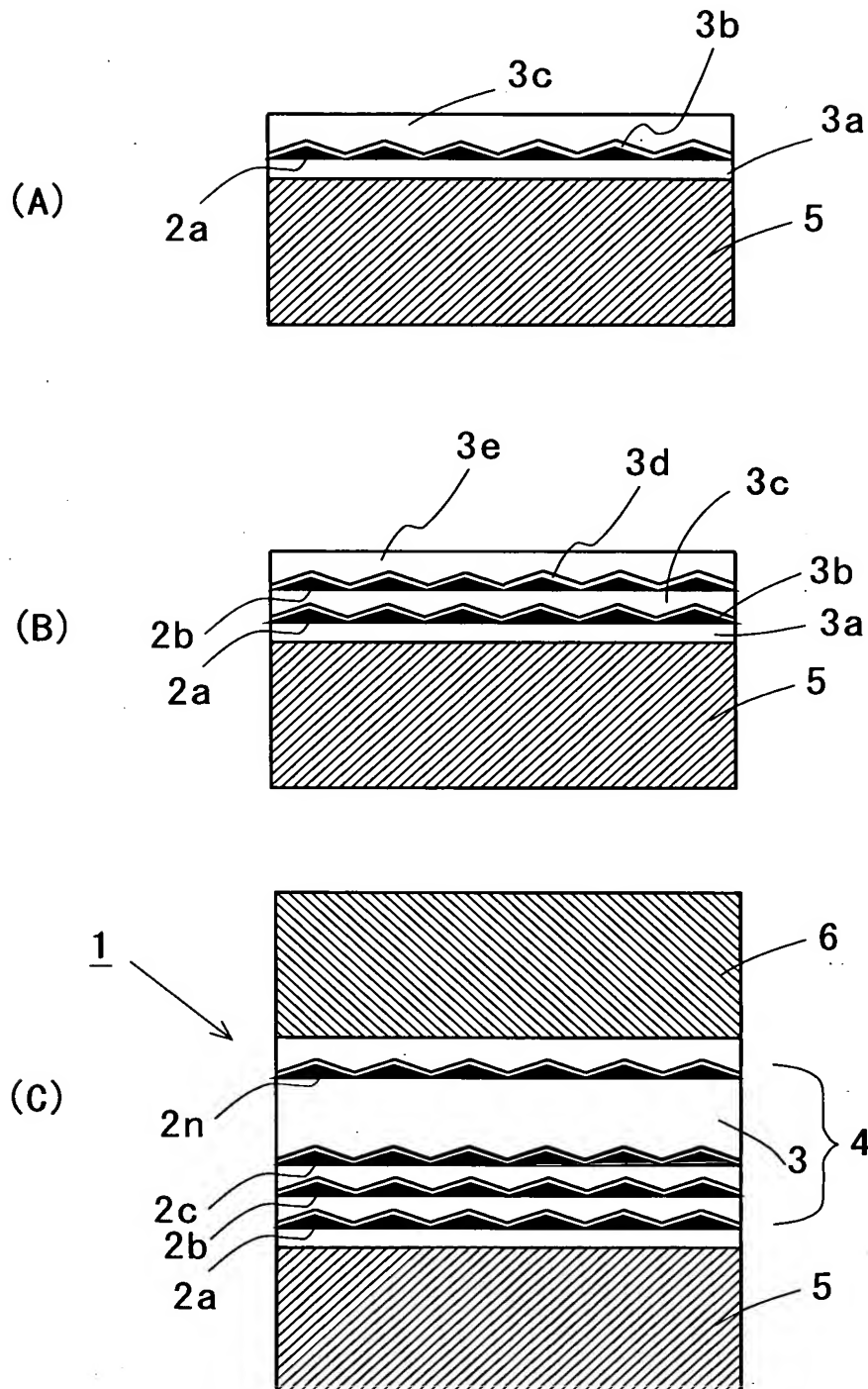


FIG. 12

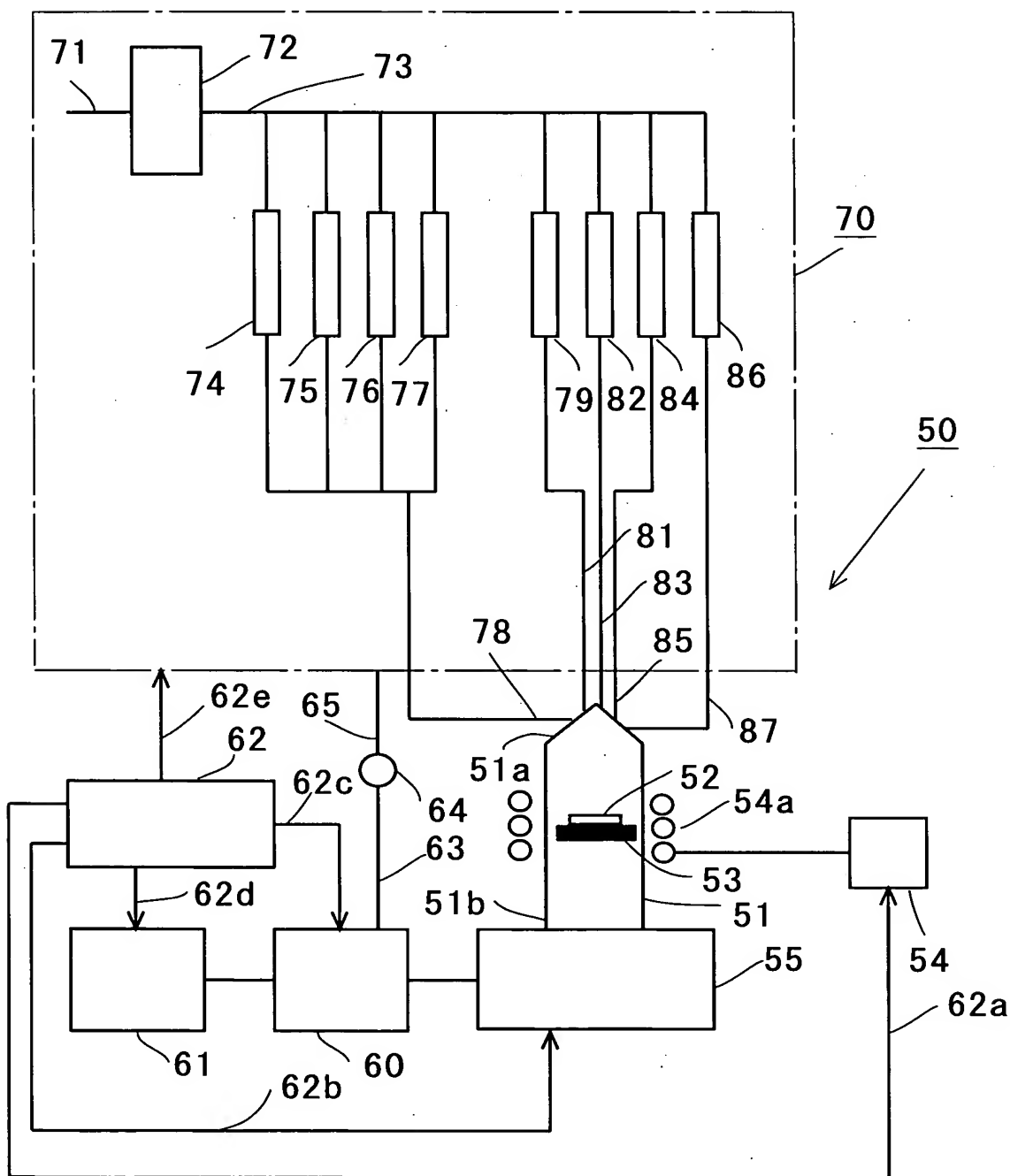


FIG. 13

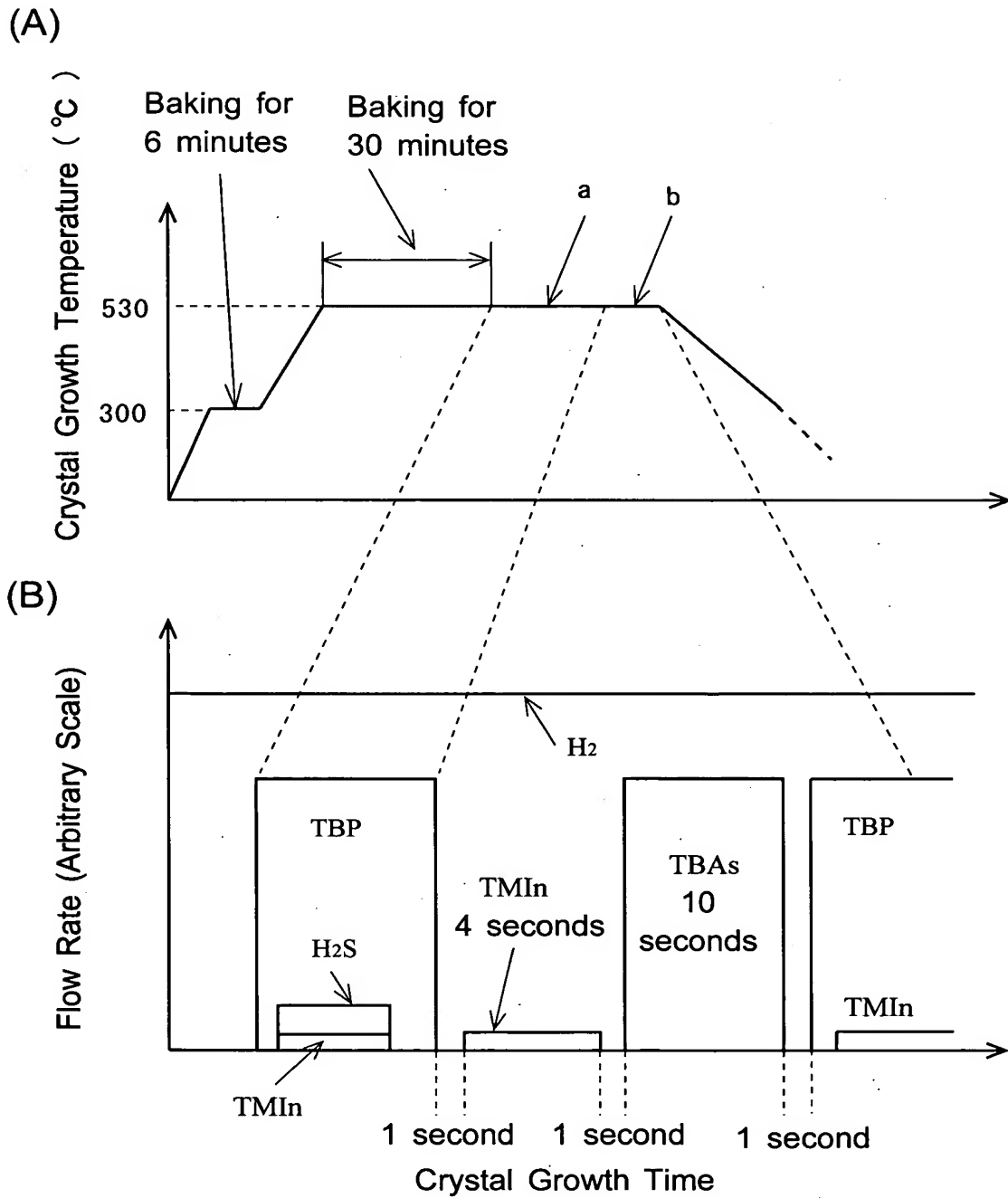
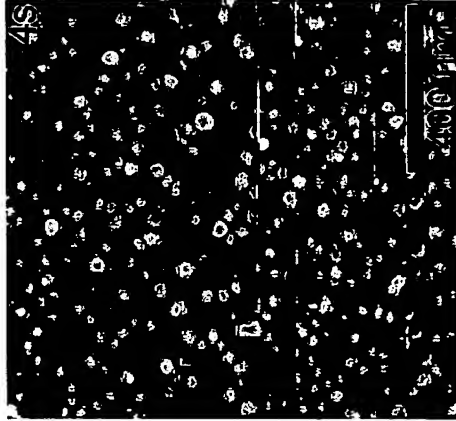
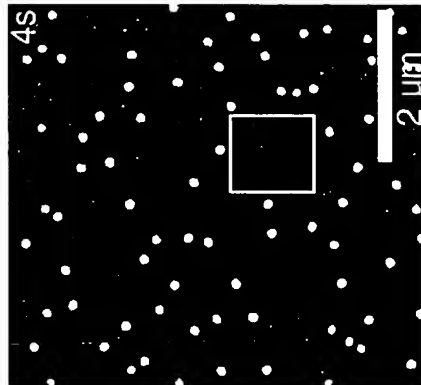


FIG. 14



(B)



(A)

FIG. 15

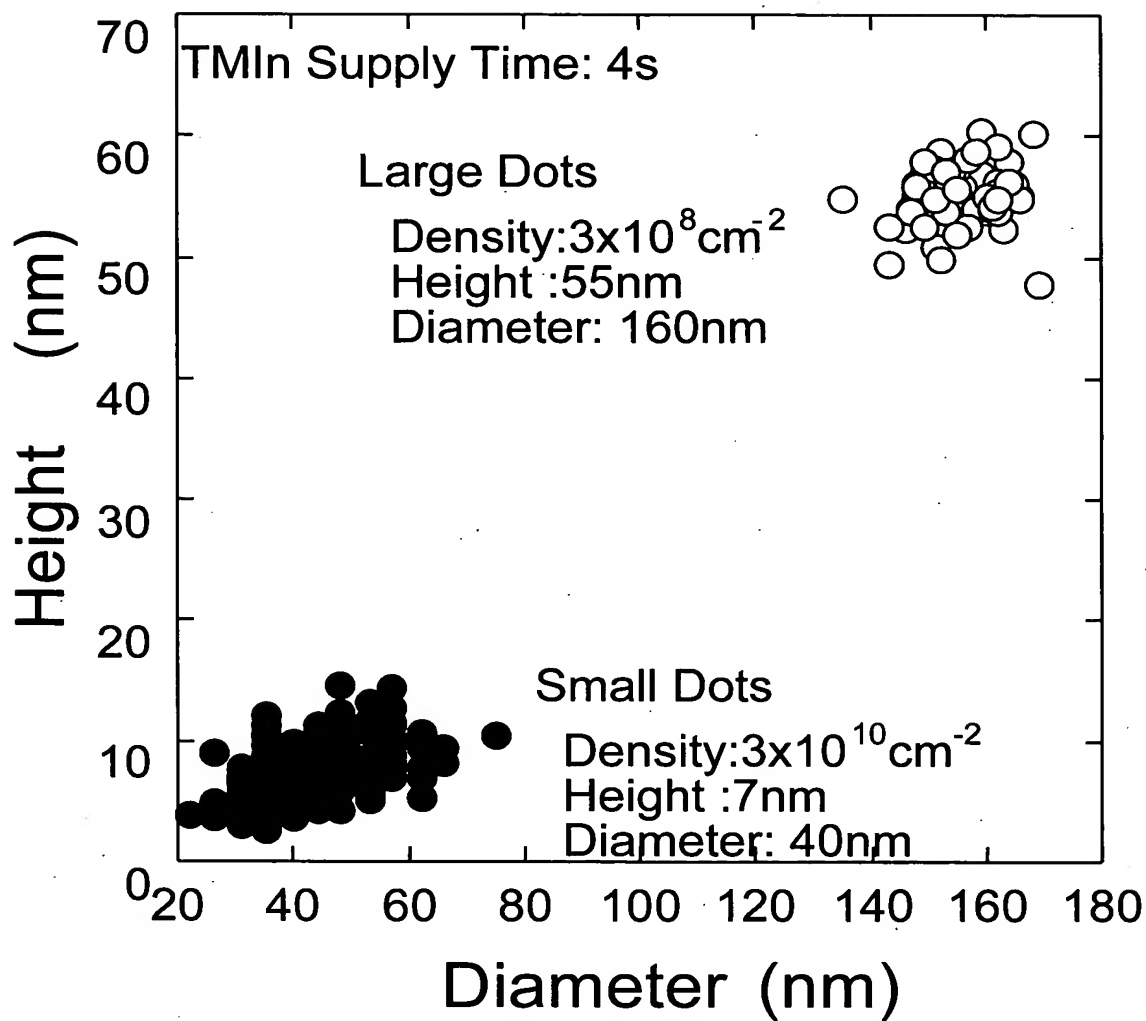


FIG. 16

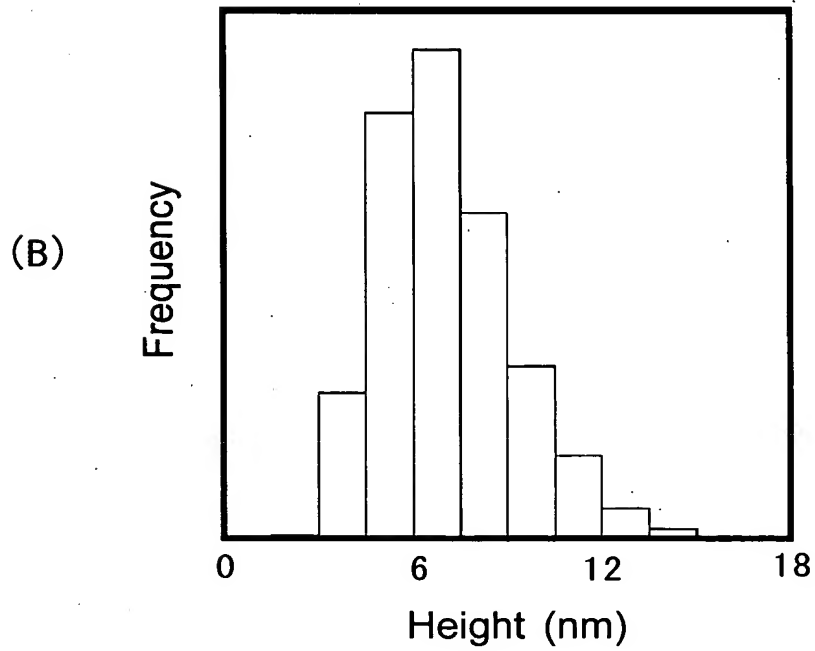
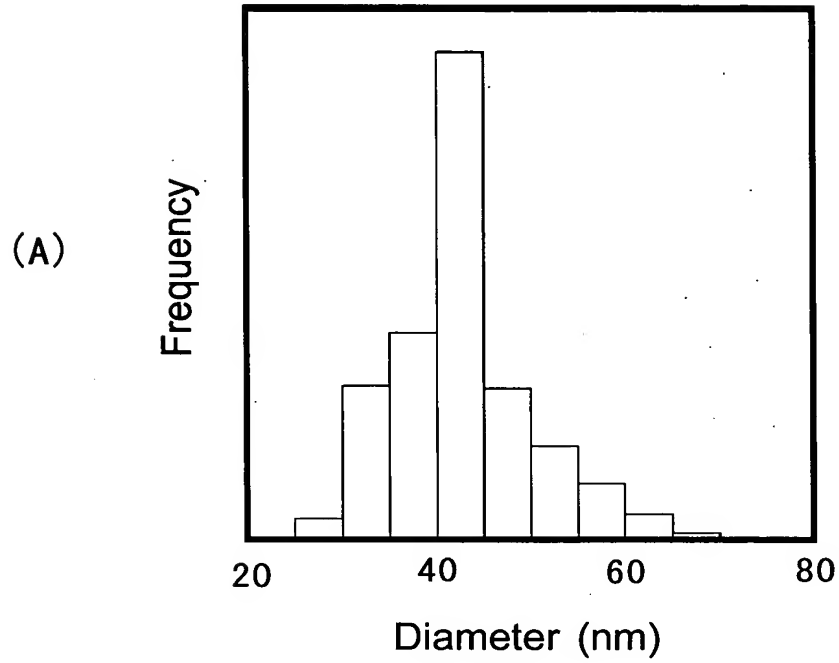




FIG. 17

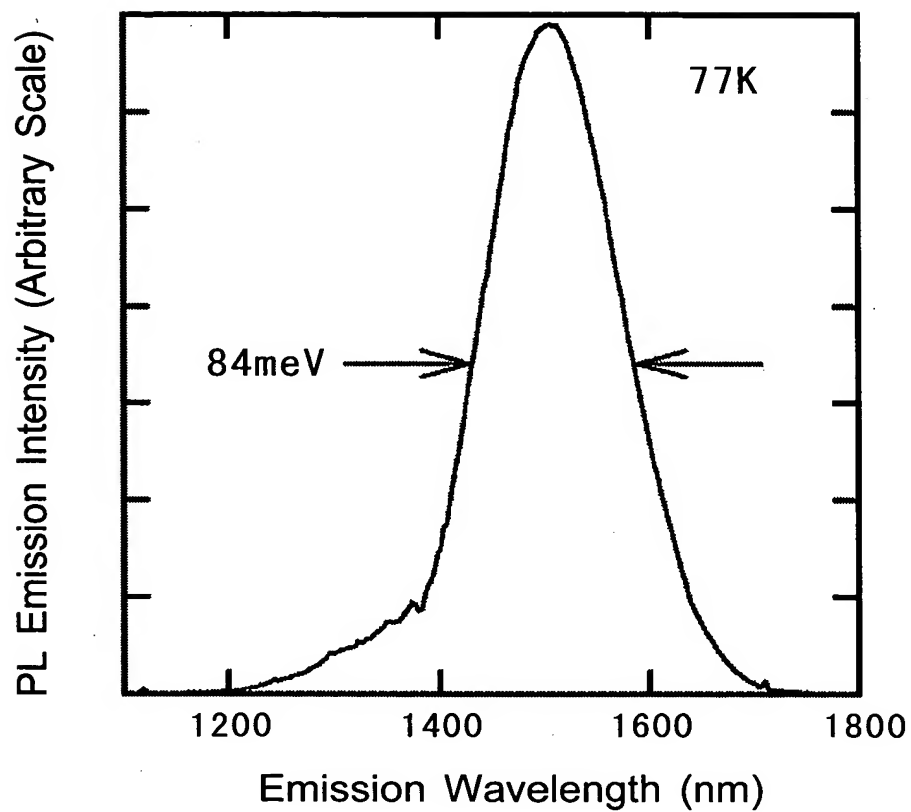


FIG. 18

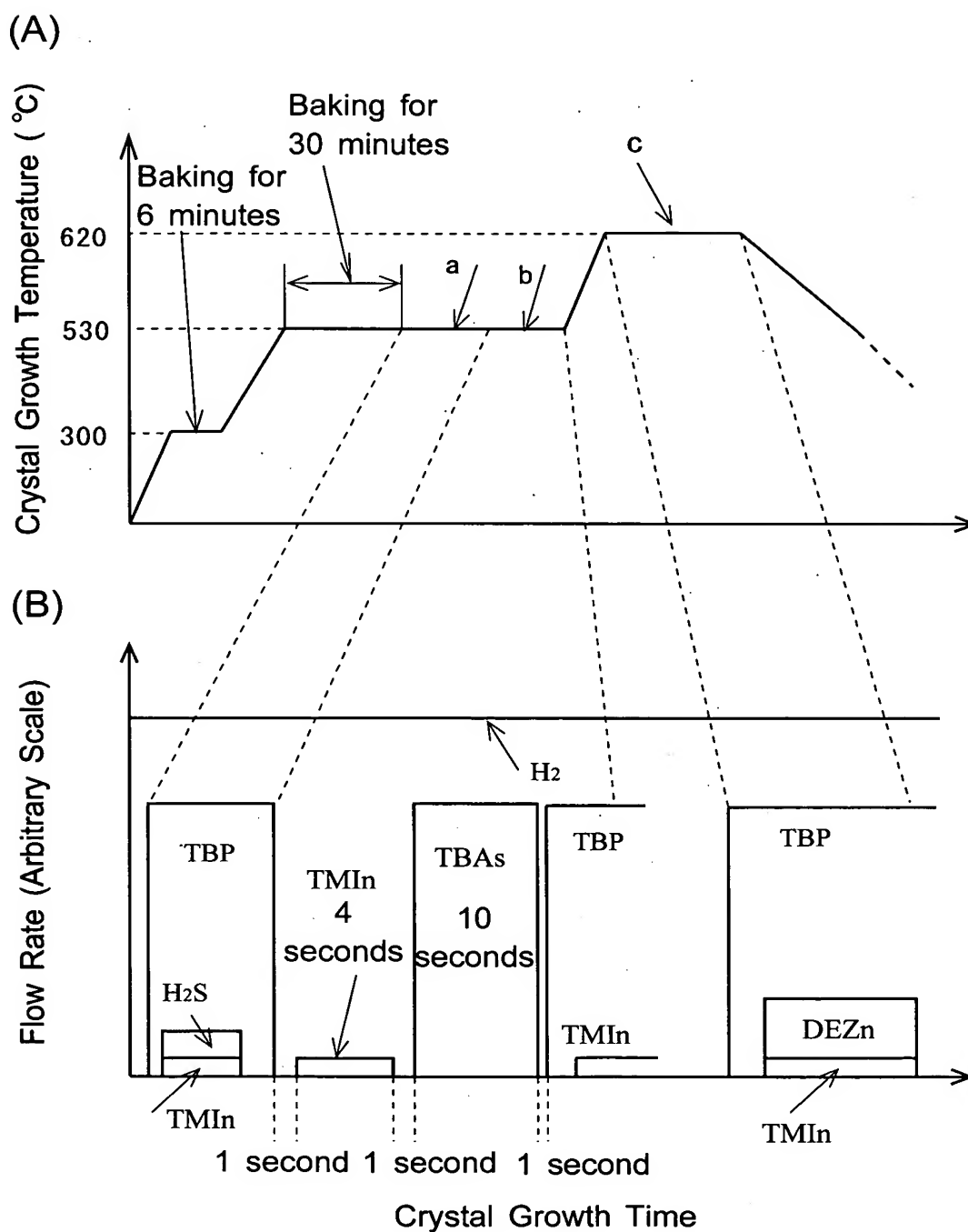


FIG. 19

Gas	Flow Rate (mol/second)
TMIn	$1.68 \times 10^{-7}$
TBA <sub>s</sub>	$3.38 \times 10^{-6}$
TBP	$3.38 \times 10^{-6}$
DEZn	$9.05 \times 10^{-8}$

FIG. 20

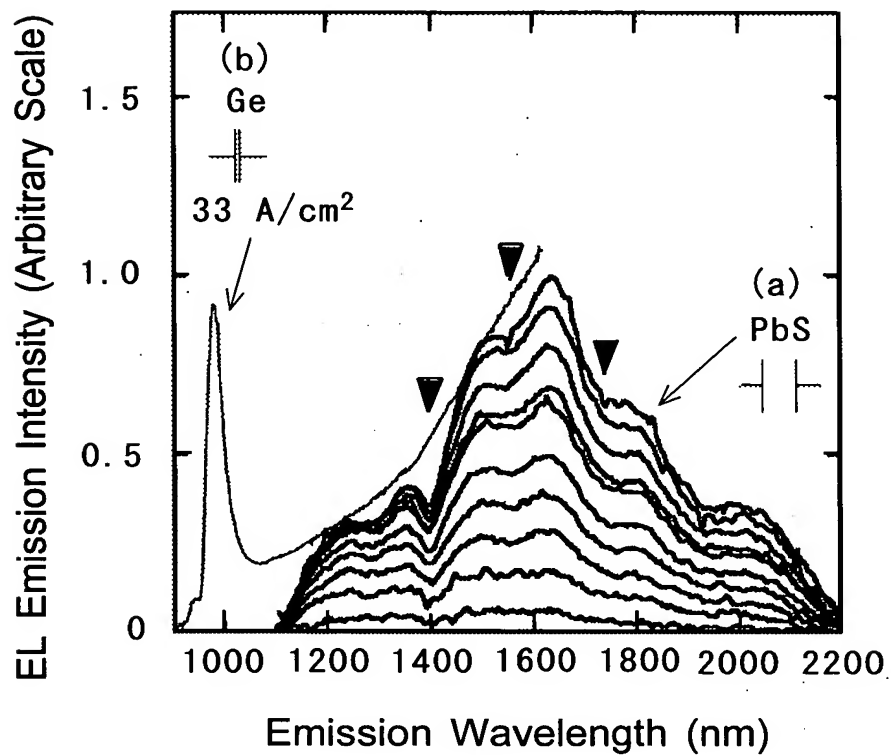


FIG. 21

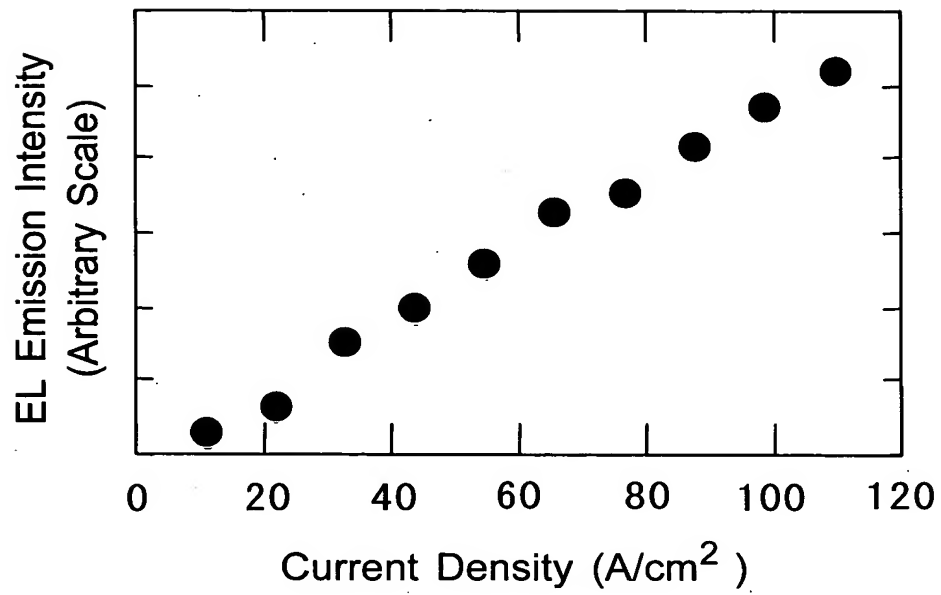


FIG. 22

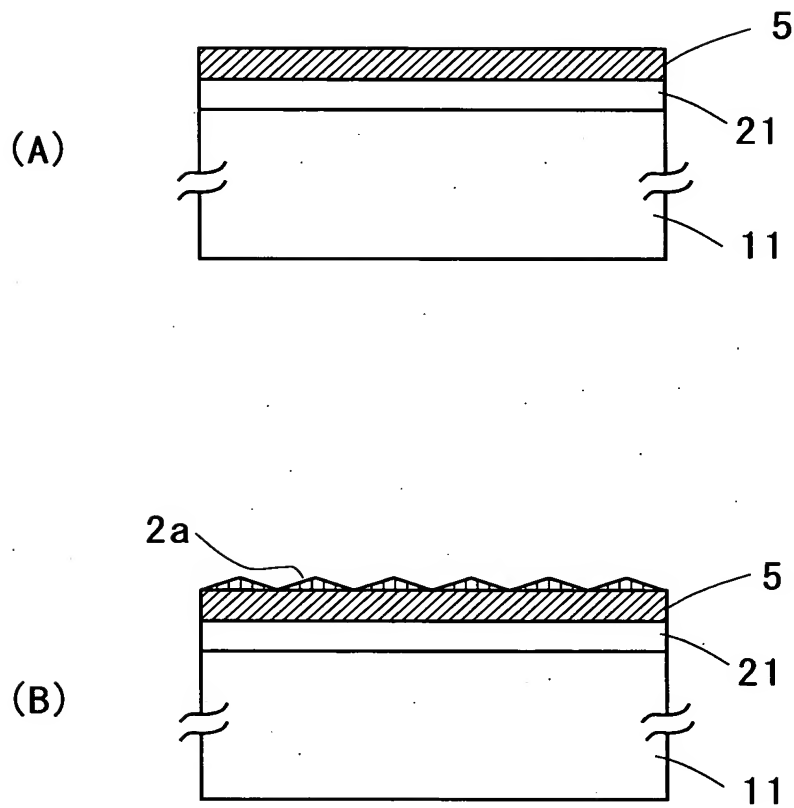


FIG. 23

Growth Apparatus	MOCVD
Growth Temperature	530°C
Pressure	7.6 Torr
Carrier Gas	H <sub>2</sub> 4 s.l.m
TMI n Flow Rate	$1.01 \times 10^{-5}$ mol/minute
TMI n Supply time	0 ~ 8 seconds
TBA s Flow Rate	$2.01 \times 10^{-4}$ mol/minute
Substrate	InP (100)

FIG. 24

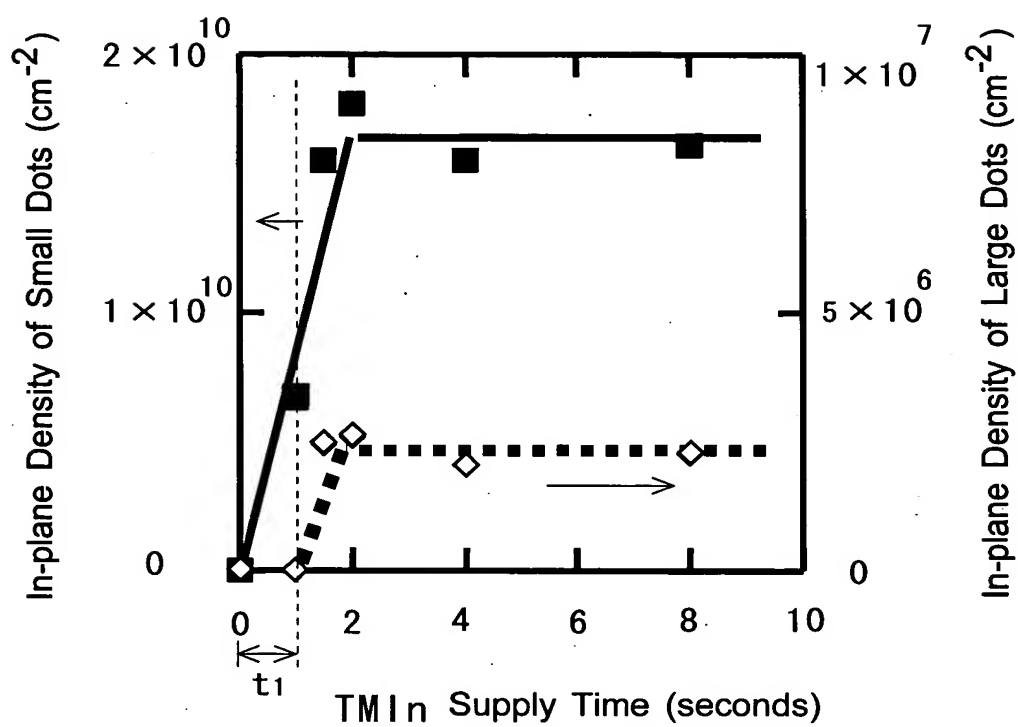




FIG. 25

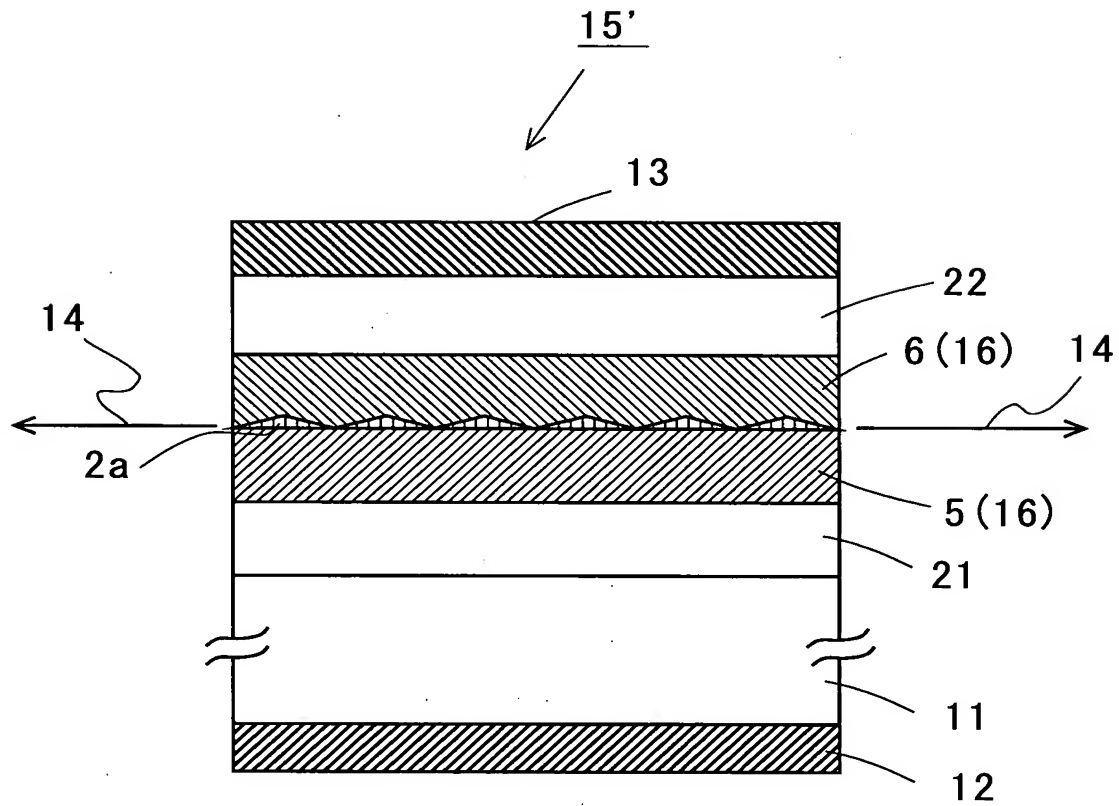


FIG. 26

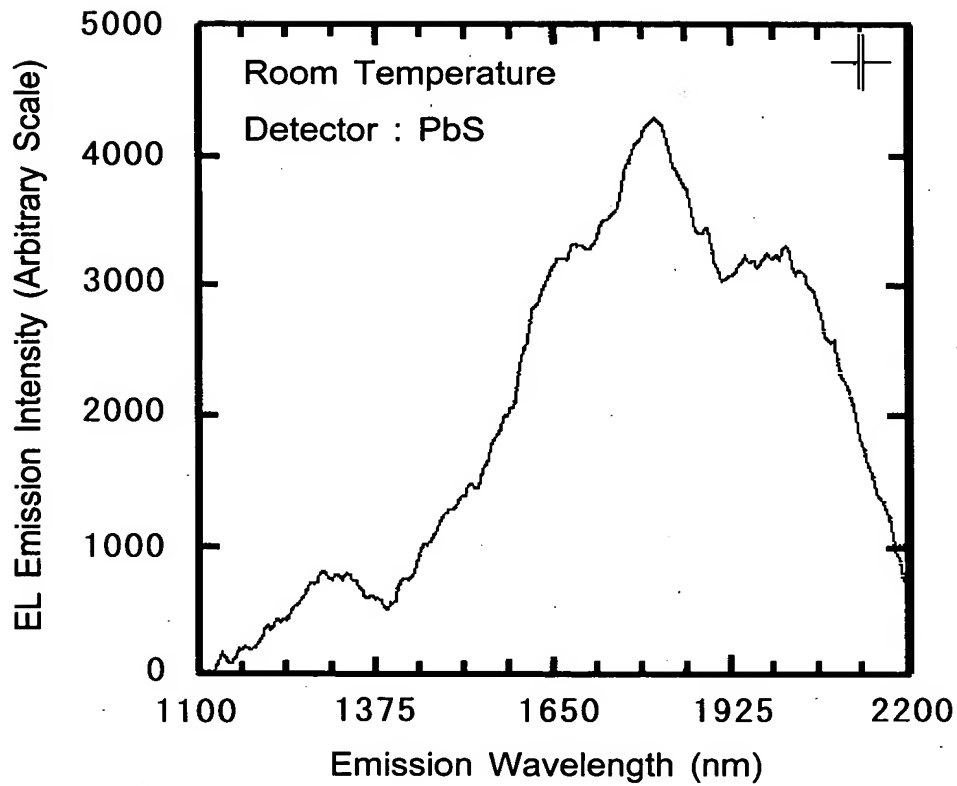


FIG. 27

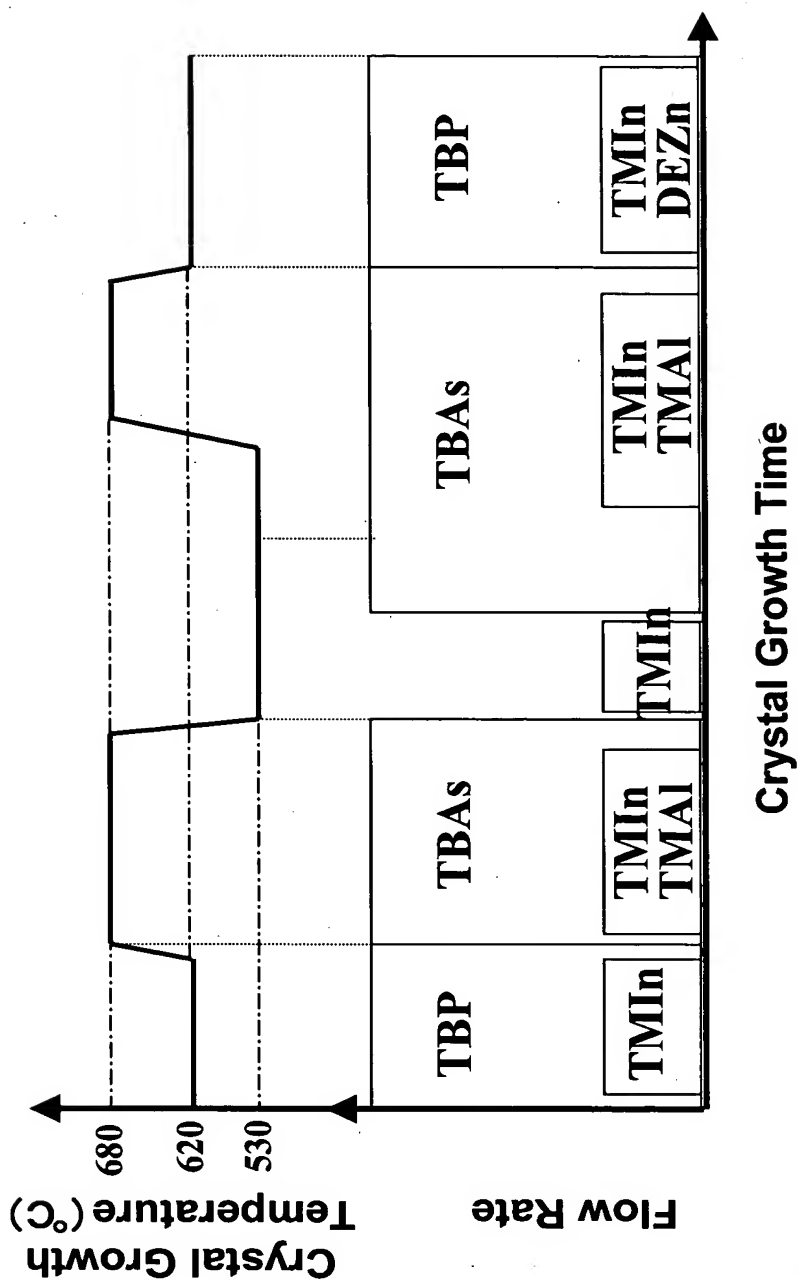


FIG. 28

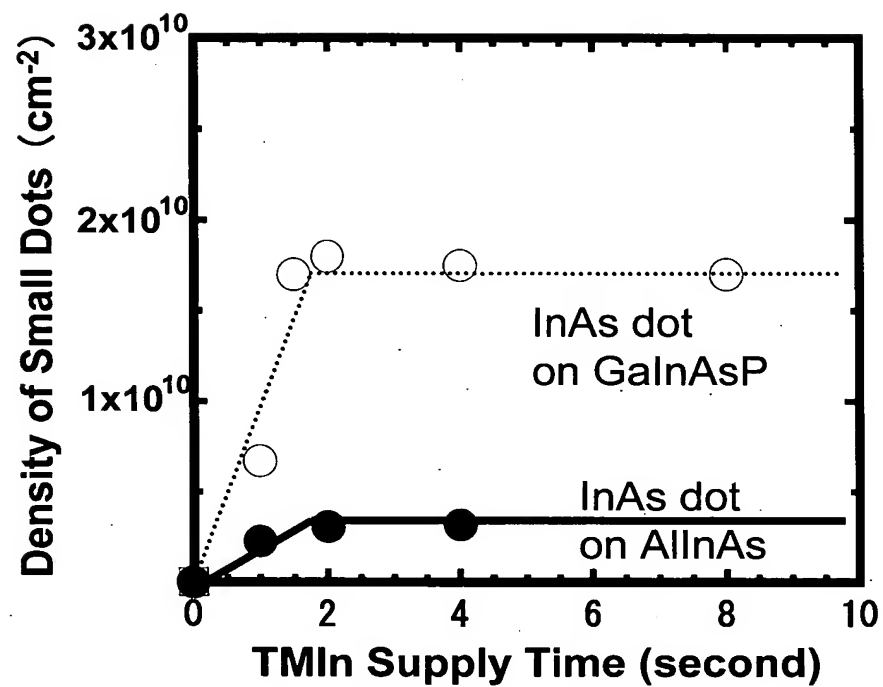


FIG. 29

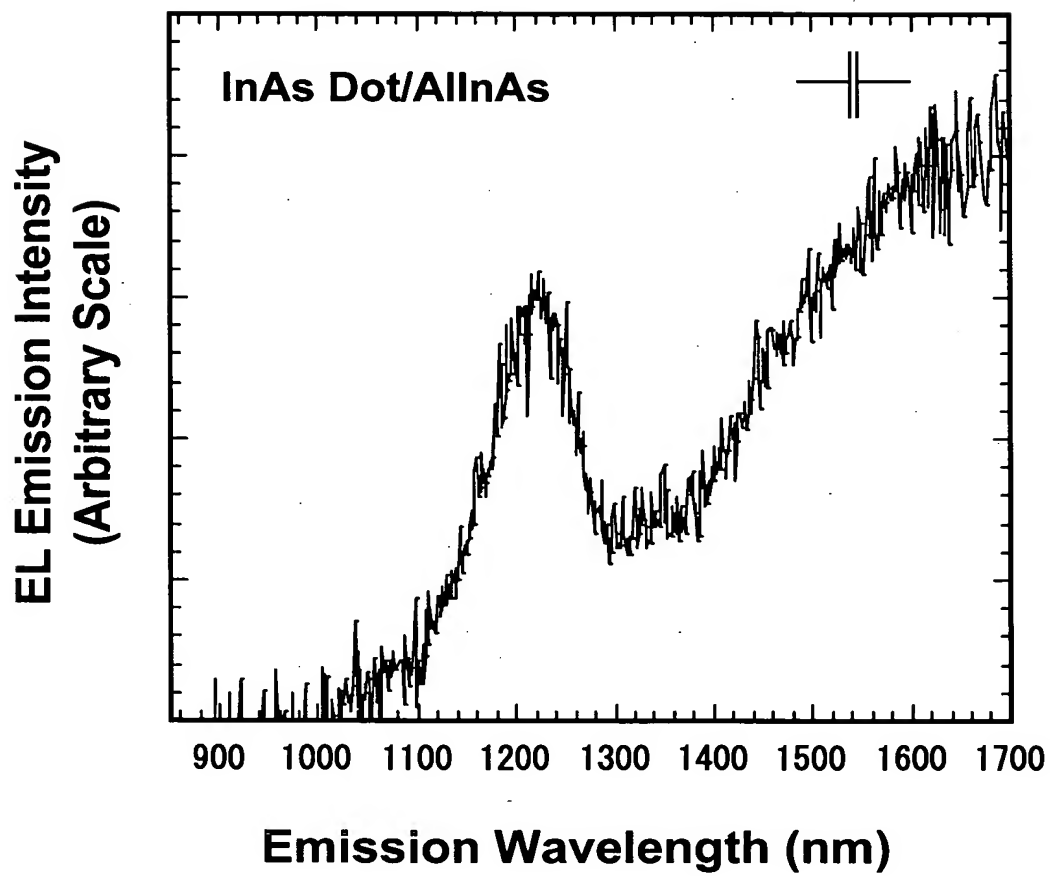


FIG. 30

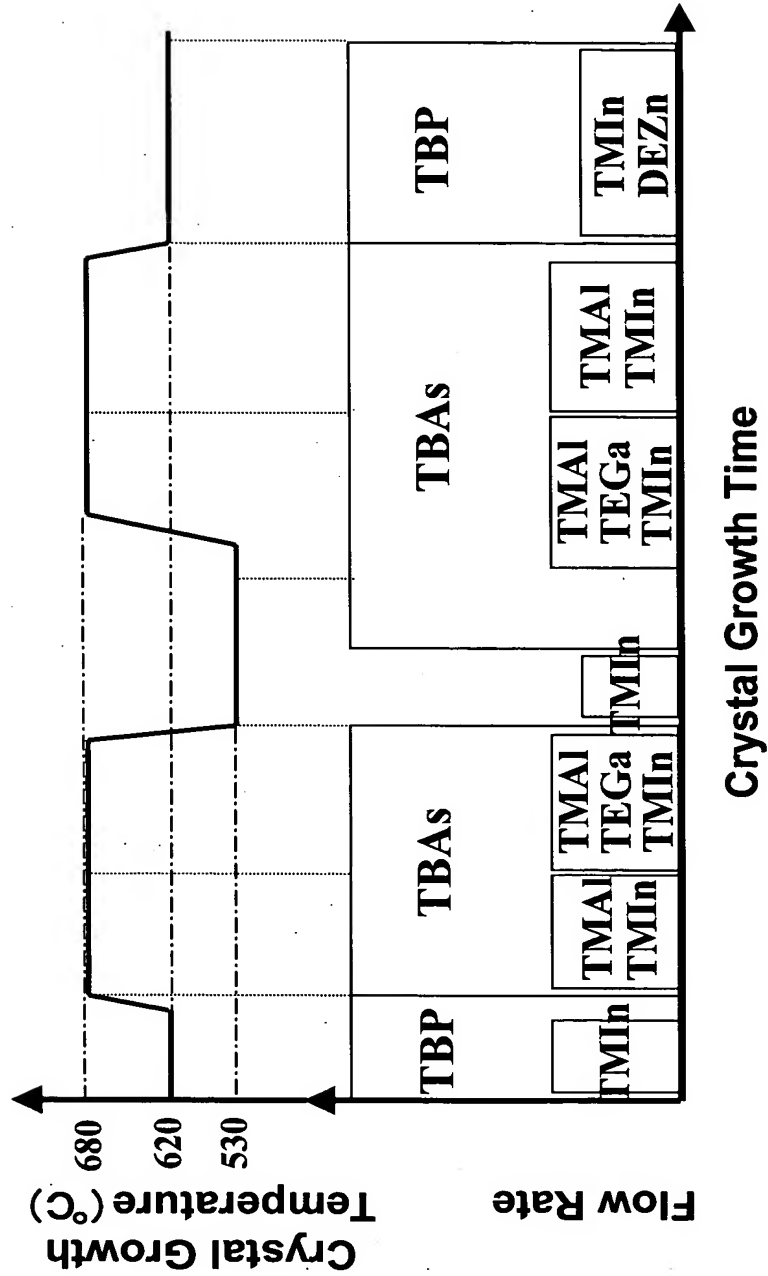


FIG. 31

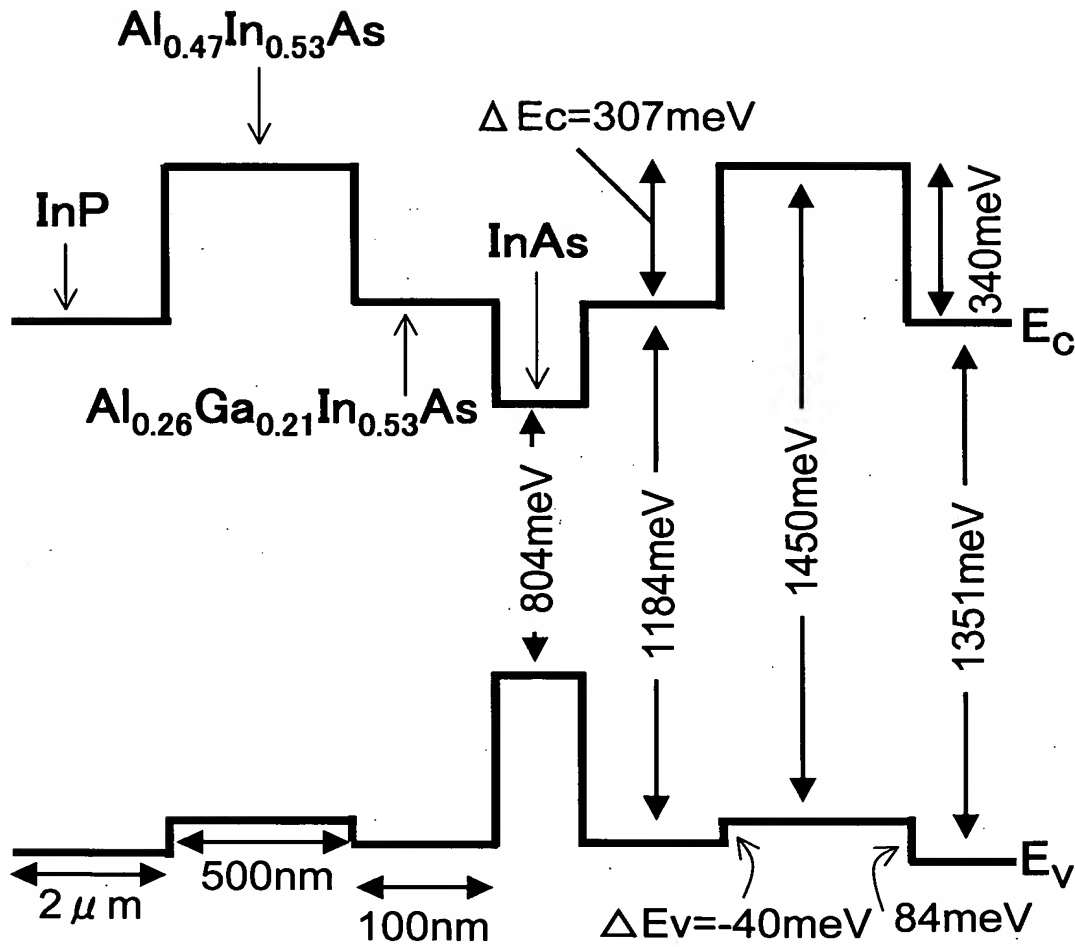


FIG. 32

